

at least one interlayer insulating film formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole, wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein the embedded conductive layer comprises a conductive material dispersed in a medium, the conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

2. (Twice Amended) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole, wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein said embedded conductive layer comprises a conductive material dispersed in a medium, said conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

3. (Twice Amended) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein said embedded conductive layer comprises a conductive material dispersed in a medium, said conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

4. (Twice Amended) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically

connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film comprising an organic resin formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein said embedded conductive layer comprises a conductive material dispersed in a medium, said conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

16. (Twice Amended) A semiconductor device according to any one of claims 1-6 or 47-50, further comprising an alignment film.

22. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a cellular phone.

23. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a camcorder.

24. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a portable computer.

25. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a head mounting display.

26. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a rear type projector.

27. (Twice Amended) A semiconductor device according to claims 1-6 or 47-50 wherein said device is a display device of a front type projector.

40. (Twice Amended) A semiconductor device according to any one of claims 1-6 or 47-50 wherein said device is an EL display device.

Please add new claims 47-74 as follows:

--47. (New) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole, wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said transistor through said embedded

conductive layer,

wherein said embedded conductive layer comprises an indium tin oxide.

48. (New) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole, wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein said embedded conductive layer comprises an indium tin oxide.

49. (New) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film formed over said capacitor forming electrode and

said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein said embedded conductive layer comprises an indium tin oxide.

50. (New) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film comprising an organic resin formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said

embedded conductive layer.

wherein said embedded conductive layer comprises an indium tin oxide.

51. (New) A device according to claim 1, wherein said medium is an organic material.

52. (New) A device according to claim 2, wherein said medium is an organic material.

53. (New) A device according to claim 3, wherein said medium is an organic material.

54. (New) A device according to claim 4, wherein said medium is an organic material.

55. (New) A device according to claim 47, wherein said medium is an organic material.

56. (New) A device according to claim 48, wherein said medium is an organic material.

57. (New) A device according to claim 49, wherein said medium is an organic material.

58. (New) A device according to claim 50, wherein said medium is an organic material.

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59. (New) A device according to claim 1, wherein said medium is an organic material.

60. (New) A device according to claim 2, wherein said medium is an inorganic material.

61. (New) A device according to claim 3, wherein said medium is an inorganic material.

62. (New) A device according to claim 4, wherein said medium is an inorganic material.

63. (New) A device according to claim 47, wherein said medium is an inorganic material.

64. (New) A device according to claim 48, wherein said medium is an inorganic material.

65. (New) A device according to claim 49, wherein said medium is an inorganic material.

66. (New) A device according to claim 50, wherein said medium is an inorganic material.

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67. (New) A device according to claim 1, wherein said medium is an inorganic material.

Sub B2 68. (New) A device according to claim 2, wherein said interlayer insulating film is made from a metal.

69. (New) A device according to claim 3, wherein said interlayer insulating film is made from a metal.

70. (New) A device according to claim 4, wherein said interlayer insulating film is made from a metal.

71. (New) A device according to claim 47, wherein said interlayer insulating film is made from a metal.

72. (New) A device according to claim 48, wherein said interlayer insulating film is made from a metal.

73. (New) A device according to claim 49, wherein said interlayer insulating film is made from a metal.

74. (New) A device according to claim 49, wherein said interlayer insulating film is made from a metal.--

REMARKS

The Office Action of **June 20, 2001**, has been received and its contents carefully noted. Claims 1-10, 13-16, 22-27, 40 and 46 were pending in the present application prior to the aforementioned amendment. By the above Amendment, claims 7-8 and 13-14 are canceled without prejudice, claims 1-4, 16, 22-27 and 40 are amended, and new claims 47-